



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790HB

Generic Copy

Issue Date: 06-Aug-2014

TITLE: Final PCN for wafer fab transfer from Gifu in Japan to Niigata in Japan (Group HB).

PROPOSED FIRST SHIP DATE: 14-Nov-2014 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com.

SAMPLES: Contact your local ON Semiconductor Sales Office or Shigehito.Matsumoto@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available

Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers.

FPCNs are issued at least 97 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce about the transfer of products from ON Semiconductor wafer fabrication sites located in Gifu Japan to the wafer fabrication ON Semiconductor Niigata Co., Ltd.(OSNC). OSNC is located in Niigata, Japan, obtained ISO9001 certification.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.



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RELIABILITY DATA SUMMARY

Group HB

Test:	Conditions:	Interval:	Results
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC, VDSS =max	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03 × 10 ⁵ Pa, 100%	50 hrs	Pass
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Resistance to Soldering heat(Reflow)	Solder Temp.: 260degC ± 5degC	10s	Pass
Solderability	Solder Temp.: 245degC ± 5degC	5 s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected Generic parts:

Group HB

PART_ID
CPH3348-TL-E
CPH6337-TL-E
MCH3374-TL-E
MCH6320-TL-E